**PAM-4 Photodiode Solutions**

### 28G Photodiode
- Cost effective, small die size
- 28 Gbaud PAM-4
- Easy optical coupling into large topside optical aperture
- G-S-G pad configuration with large pad diameter of 80 µm

### 4 x 28G Photodiode Array
- 4 channel array with channel pitch of 250 µm
- 100G Ethernet
- 28 Gbaud PAM-4 per channel
- Layout suitable for wire bonding and flip-chip soldering
- G-S-G pad configuration for each channel

### 28G Photodiode with Backside Lens
- Easy optical coupling through integrated backside lens
- 28 Gbaud PAM-4
- Available as chip or flip-chip mounted on carrier

### 28G APD with Backside Lens
- Easy optical coupling through integrated backside lens
- 28 Gbaud PAM-4
- Low operating bias of 20 V
- Layout suitable for wire bonding and flip-chip soldering
- Available as chip or flip-chip mounted on carrier

### 56G Photodiode with Enhanced Responsivity
- Cost effective, small die size
- High responsivity of 0.8 A/W
- 56 Gbaud PAM-4
- 100G Single Lambda

### 56G Photodiode with Backside Lens
- Easy optical coupling through integrated backside lens
- 56 Gbaud PAM-4
- Available as chip or flip-chip mounted on carrier

### 28G / 56G Photodiode on Carrier
- Easy optical coupling through integrated backside lens
- High precision multi-channel placement
- Speeds from 28 Gbaud up to 56 Gbaud PAM-4 per channel
- 400GBASE-DR4, 400G-FR4
- Flip-chip soldered on ceramic carrier
- Customized submount layouts

### 56G Photodiode with Backside Lens
- Easy optical coupling through integrated backside lens
- 56 Gbaud PAM-4
- 100G Single Lambda

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**PRODUCT OVERVIEW**

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